CONTENTS

Polyakov V. V. *Stray Capacitance Compensation Technique in Scanning Capacitance Microscopy*6 Specially designed probe and novel stray capacitance compensation technique for 2D dopant profiles characterization of semiconductor structures by scanning capacitance microscopy (SCM) have been advanced. Corresponding unit for SCM realization has been engineered. Advantages of using compensation technique and high (10-20 nm) spatial resolution of SCM are demonstrated on samples with dopant concentration in the range $10^{15}-10^{20} \text{ cm}^{-3}$.

Keywords: SCM, capacitance microscopy, SPM, AFM, probe microscopy, dopant profile.

Obizhaev D. Yu., Zhukova S. A., Babayevsky P. G., Chetverov Yu. S. Properties and Structure of

Nano-Thin Silicon Nitride Films Formed on Polyimide Surface by Low-Temperature Plasma Deposition 14 Silicon nitride films of 2–300 nm thickness deposited on polyimide coatings and films were investigated. Films were formed by low-temperature ECR chemical vapor deposition. It was shown that the ratio of precursor gases has an influence on chemical structure, morphology and surface energetic properties of the films and does not have an influence on Young's modulus.

Keywords: silicon nitride, plasma deposition, deposition of a gas phase, microelectromechanical converters, superficial microprocessing, a sacrificial layer, an elektron-cyclotron resonance.

Keywords: ferroelectrics, perovskite, heterogeneous structural states.

The scintillation characteristics of new scintillition materials based on deformed powders alkali metal halides were studied. Reduce decay times of deformed powders was observed in deformed powders scintillators as compared with the single crystal.

Keywords: scintillator, decay time, intensive plastic deformation.

Keywords: implantation, silicon on sapphire, high-temperature annealing.

Keywords: system-on-Chip (SoC), convergence, above branches of science, nano- and IT-technology, wireless nanosystems, personal teraflop supercomputer, paradoxes, century challenge.

Keywords: semiconductor laser, super-high speed digital signal transmission characteristics, fiber optic systems.

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